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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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of 5 Sheet 1

Complete if Known				
Application Number	10/762,181			
Filing Date	January 21, 2004			
First Named Inventor	Mohklesi			
Art Unit	2827			
Examiner Name	Huan Hoang			
Attorney Docket Number	SAND-01021US0			

	U. S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Document Number  Number-Kind Code <sup>2 (f bood)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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	<u> </u>	US- 5,095,344	3/10/1992	Harari			
		US- 5,172,338	12/15/1992	Mehrotra et al.			
		<sup>US-</sup> 5,343,063	8/30/1994	Yuan et al.			
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		<sup>US-</sup> 6,103,573	8/15/2000	Harari et al.			
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WY	1	<sup>US-</sup> 6,151,248	11/21/2000	Harari et al.			

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Examiner Initials'	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Peges, Columns, Lines, Where Relevant Passages	
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Examiner Signature	Huan	Hoang	Dats Considered	15/27/05

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INFORMATION DICCLOSURE	Filing Date	January 21, 2004	_		
INFORMATION DISCLOSURE	First Named Inventor	Mohklesi	_		
STATEMENT BY APPLICANT (Use as many shoots as necessary)	Art Unit	2827			
	Examiner Name .	Huan Houng			
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		US- 6246607	6/12/2001	Mang et al.		
		<sup>US-</sup> 6461905	10/8/2002	Wang et al.		
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INFORMATION DISCLOSURE				Filing Date	January 21, 2004
STATEMENT BY APPLICANT		First Named Inventor	Mohklesi		
			<b>-</b>	Art Unit	2827
(Use as many sheets as necessary)		Examiner Name	Itran Hang		
Sheet	3	of	5	Attorney Docket Number	SAND-01021US0

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	L <sub>s</sub>
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Substitute for form 1449/PTO	Application Number	10/762,181	
INFORMATION DISCLOSURE	Filing Date	January 21, 2004	
STATEMENT BY APPLICANT	First Named Inventor	Mohklesi	
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(Use as many sheets as necessary)	Examiner Name	Huan Hoan 9	
Sheet 4 of 5	Attorney Docket Number	SAND-01021US0	

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INF	ORMATION	DIS	CLOSURE	Filing Date	January 21, 2004	
STA	STATEMENT BY APPLICANT			First Named Inventor	Mohklesi	
				Art Unit	2827	
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Sheet	5	of	5	Attorney Docket Number	SAND-01021US0	

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HY		YU, et al., "Energy gap and band alignment for (Hf02)x(Al2O3)1-x on (100) SI," Applied Physics Letters, Volume 81, Number 2, July 8, 2002, pp. 376-378			
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
44		BUCKLEY, et al., "Engineering of 'Conduction Band-Crested Barriers' or 'Dielectric Constant-Crested Barriers' in view of their application to floating-gate non-volatile memory devices," pp. 55-56.	
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Sheet 1

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Art Unit	2818 2827					
Examiner Name	than thomas					
Attorney Docket Number	SAND-01021US0					

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Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (# known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
W		<sup>US-</sup> 4,870,470	9/26/1989	Bass, Jr. et al.	
1		<sup>US-</sup> 5,373,465	12/13/1994	Chen et al.	
		<sup>US-</sup> 6,617,639	9/9/2003	Wang et al.	
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